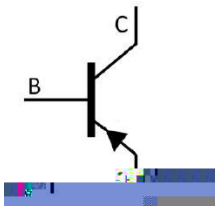
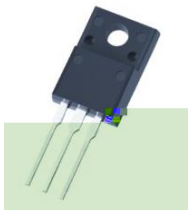
Silicon PNP transistor in a TO-220F Plastic Package.

High transition frequency, complementary to 3DA4793.

Power amplifier, driver stage amplifier applications.



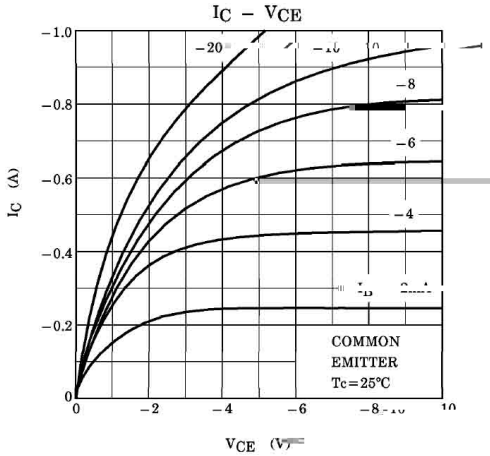


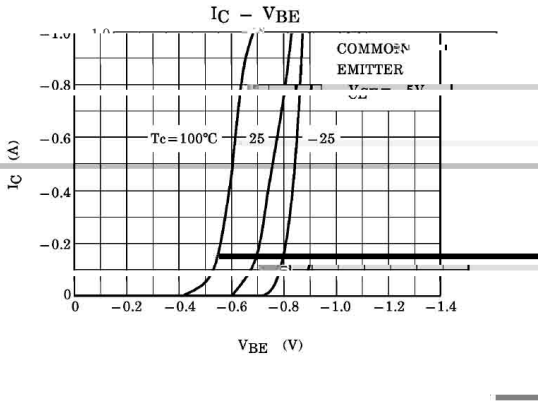
PIN1 Base PIN 2 Collector PIN 3 Emitter

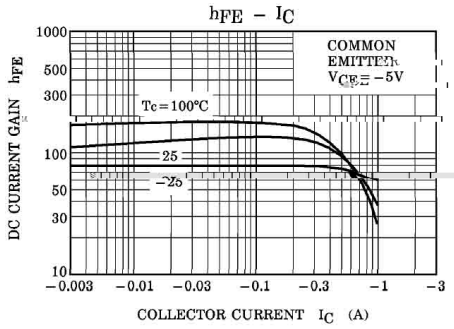
See Marking Instructions.

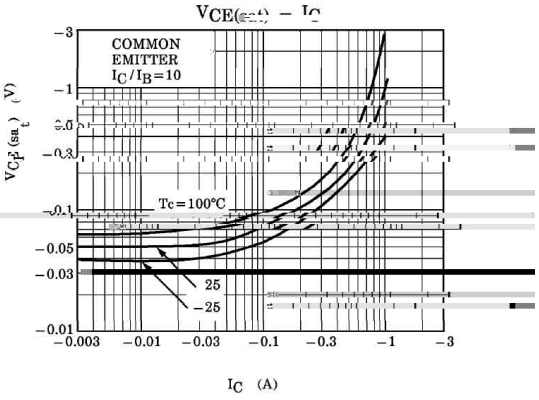
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-230	V
Collector to Emitter Voltage	V_{CEO}	-230	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-1.0	A
Base Current	I_B	-0.1	A
Collector Power Dissipation	P_C	2.0	W
	$P_{C(Tc=25\ )}$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

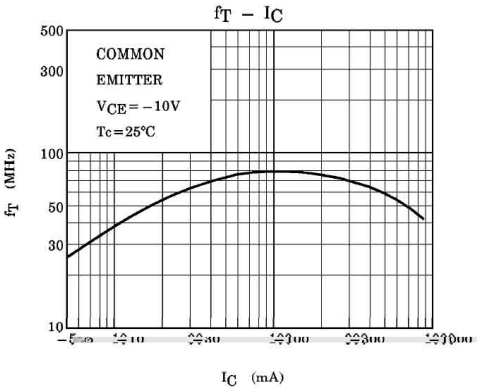
Parameter	Symbol	Test Conditions	Min

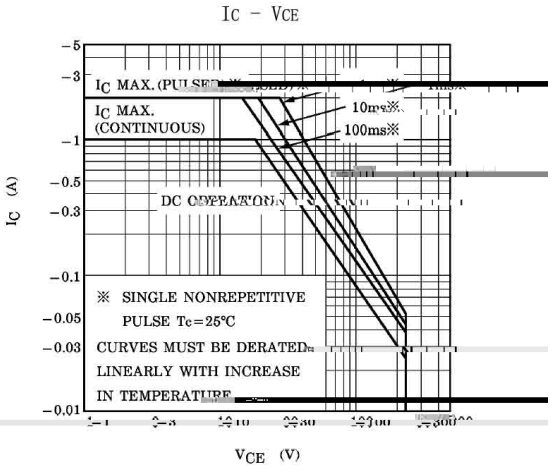

IC – VCE
−20
−8
−6
−4
COMMON
EMITTER
Tc=25°C
IC (A)
VCE (V)

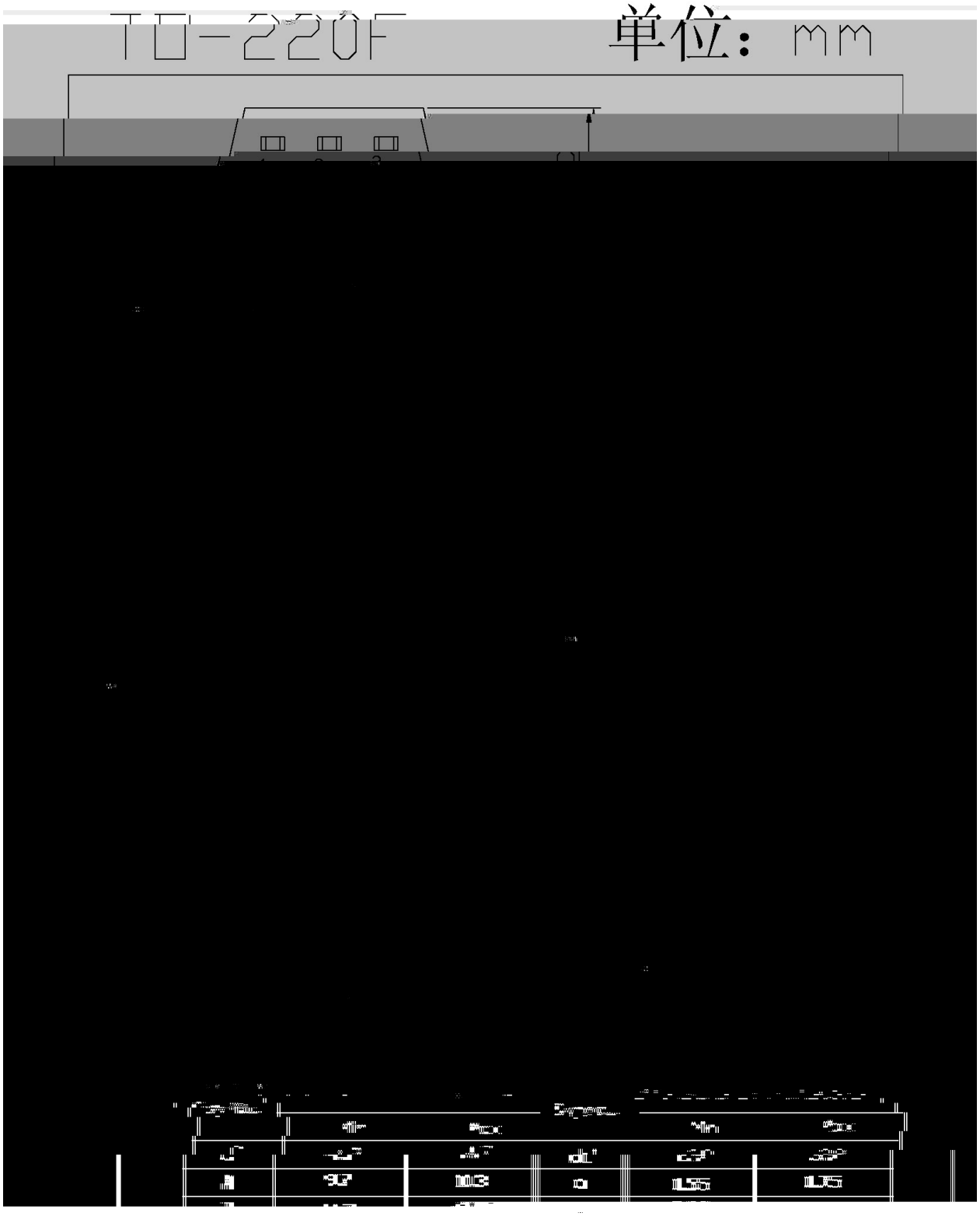

IC – VBE
COMMON
EMITTER
Tc=100°C
25
−25
IC (A)
VBE (V)

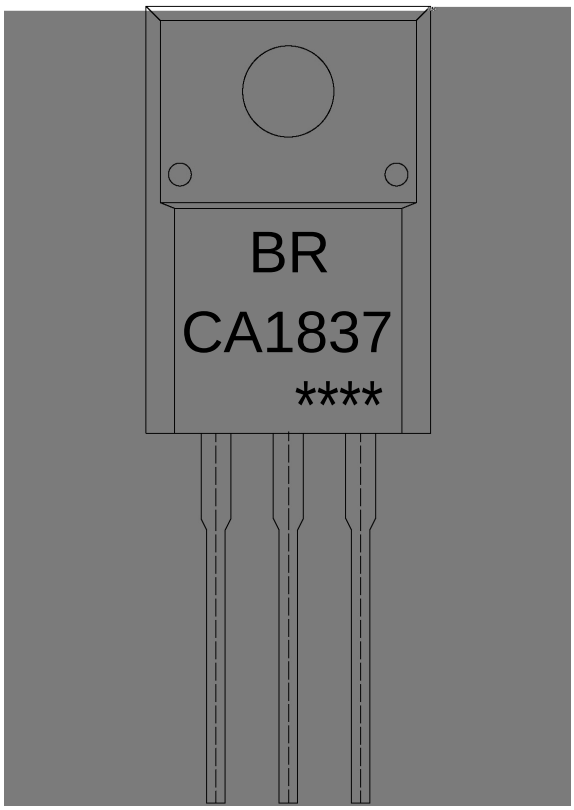

hFE – IC
COMMON
EMITTER
VCE=−5V
Tc=100°C
25
−25
DC CURRENT GAIN hFE
COLLECTOR CURRENT IC (A)


COMMON
EMITTER
IC/IB=10
Tc=100°C
25
−25
IC (A)


fT – IC
COMMON
EMITTER
VCE=−10V
Tc=25°C
fT (MHz)
IC (mA)


IC – VCE
IC MAX. (CONTINUOUS)
10ms※
100ms※
DC OPERATION
※ SINGLE NONREPETITIVE
PULSE Tc=25°C
CURVES MUST BE DERATED
LINEARLY WITH INCREASE
IN TEMPERATURE
IC (A)
VCE (V)


TO-220F
单位：mm



BR

Note:

BR:	Company Code.
CA1837:	Product Type.
****:	Lot No. Code, code change with Lot No.